9 5 6 .> / / x 4 ?ú 3 MOS « | • ’ož
N-Channel MOSFET in a SOP-8 Plastic Package.

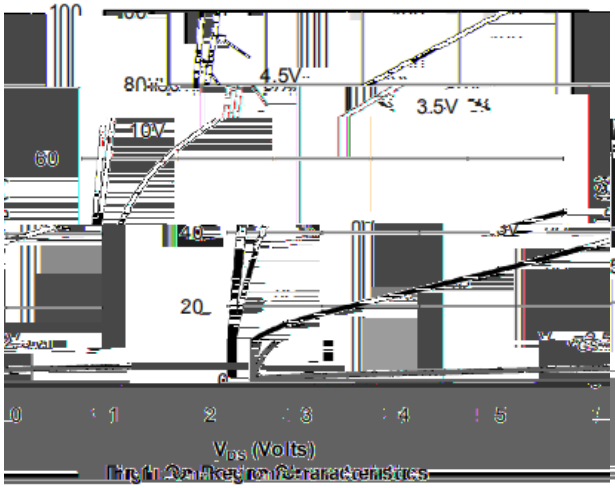
V_{DS}=30V I_D=23A(V_{GS}=±20V)
$R_{DS(ON)}$@10V ”5.5m (Typ.4.3m)
$R_{DS(ON)}$@4.5V ”7.0m (Typ.5.5m)
—)í D }ož HF Product.

*) *) y ') *) ô E ˜ c 5 … v k œ Y + v + v ô E ˜ ¨ ’ y Ï@tPY€‘•V?lô E ˜ Æ @N-Chann0[<0020c (DS(ON) .55

@ *f* Parameter		… Z Symbol	*f* › Rating	% y Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_C=25	I_D	23	A
Pulsed Drain Current [7]		I_{DM}	120	A
Avalanche Current		I_{AS}	30	A
Avalanche energy		E_{AS}	70	mJ
Power Dissipation	T_C=25	P_D	5	W
Operating and Junction Temperature Range		T_j T_{stg}	-55 +150	
Thermal resistance, junction - ambient		R $_{JA}$	75	/ W
Thermal resistance, junction - case		R $_{JC}$	25	/ W

@ *f*	… Z	y ¡ Ú ^ Test Conditions		Â 4 › Min	Á º › Typ	Â Ý › Max	% y Unit
[redacted]		V_{GS}=0V	I_D=250 A	30			V
[redacted]		V_{DS}=30V	V_{GS}=0V			1.0	A
Gate-Body Leakage Current Forward	I_{GSS}	V_{GS}=±20V	V_{DS}=0V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}	I_D=250 A	1.2	1.8	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V	I_D=20A		4.3	5.5	m
		V_{GS}=4.5V	I_D=12A		5.5	7	
Forward Transconductance	g_{FS}	V_{DS}=25V	I_D=10A		30		S
Diode Forward Voltage	V_{SD}	I_S=1A	V_{GS}=0V		0.7	1.2	V

Ô ? d • Ž ¢ / Electrical Characterist3u Curve



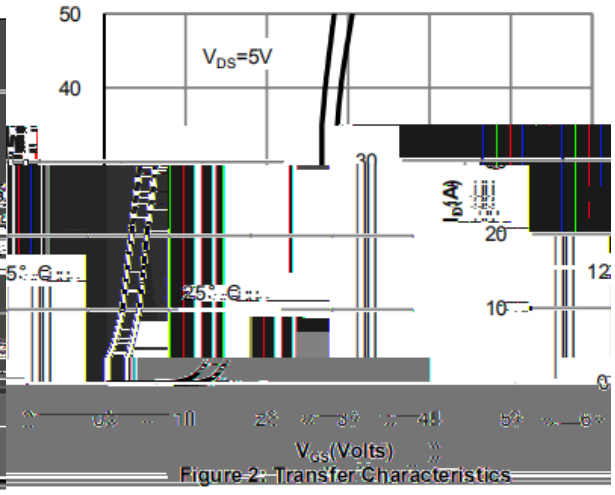
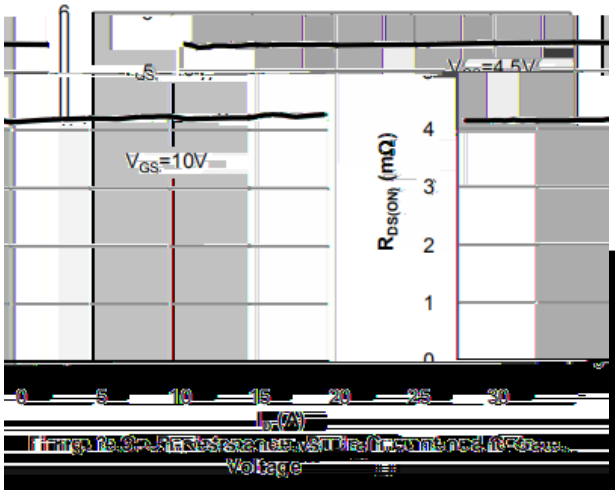
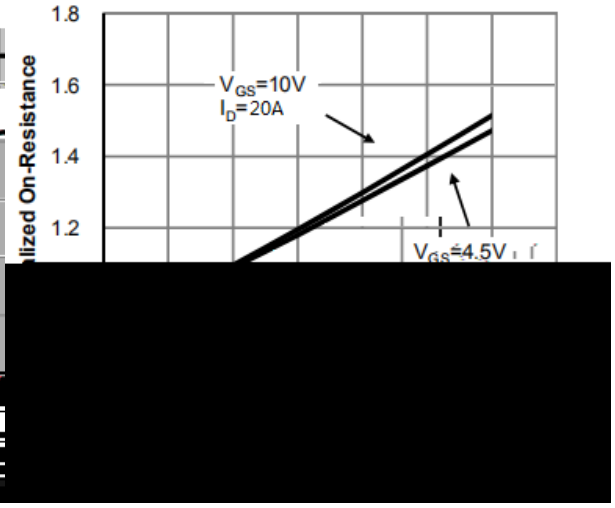


Figure 2: Transfer Characteristics





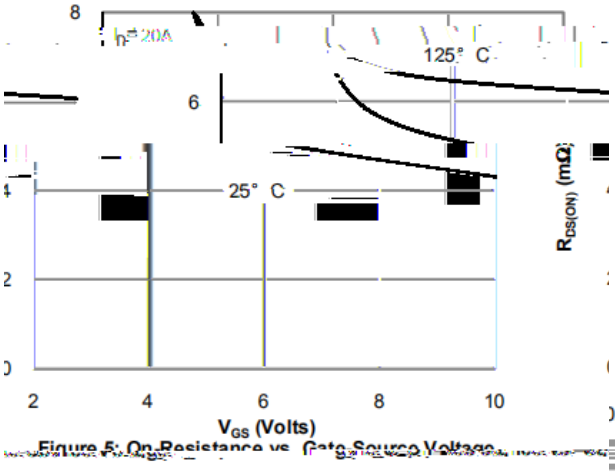


Figure 5: On-Resistance vs. Gate-Source Voltage

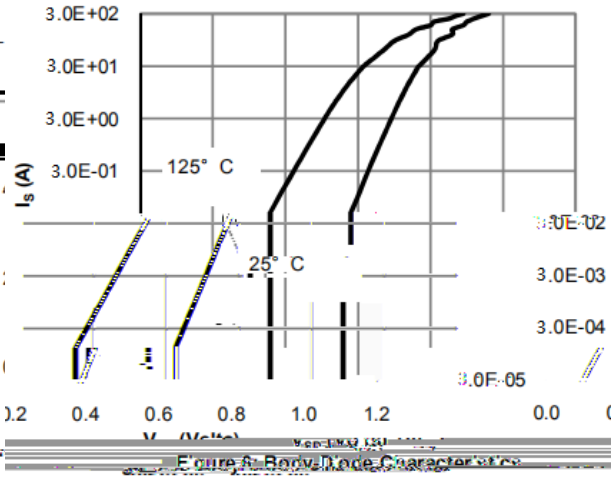
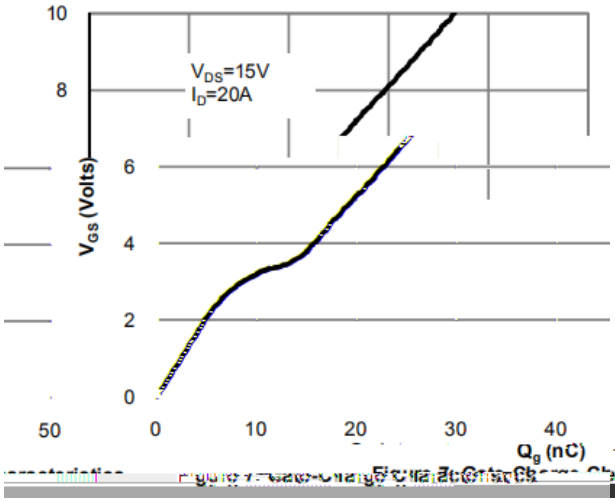
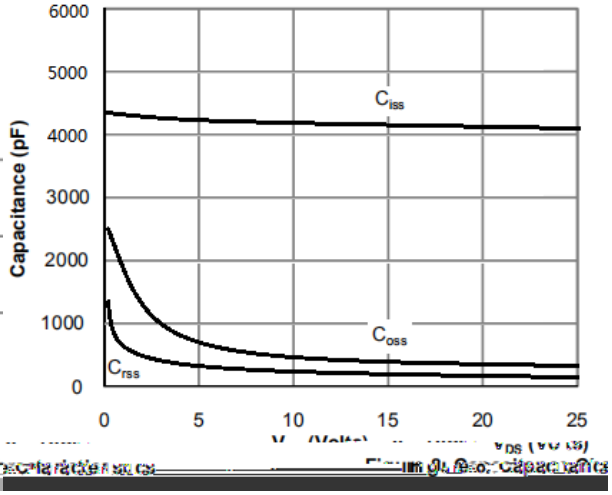
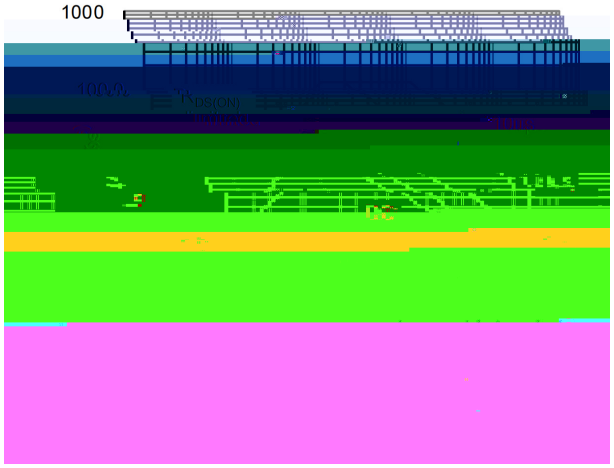


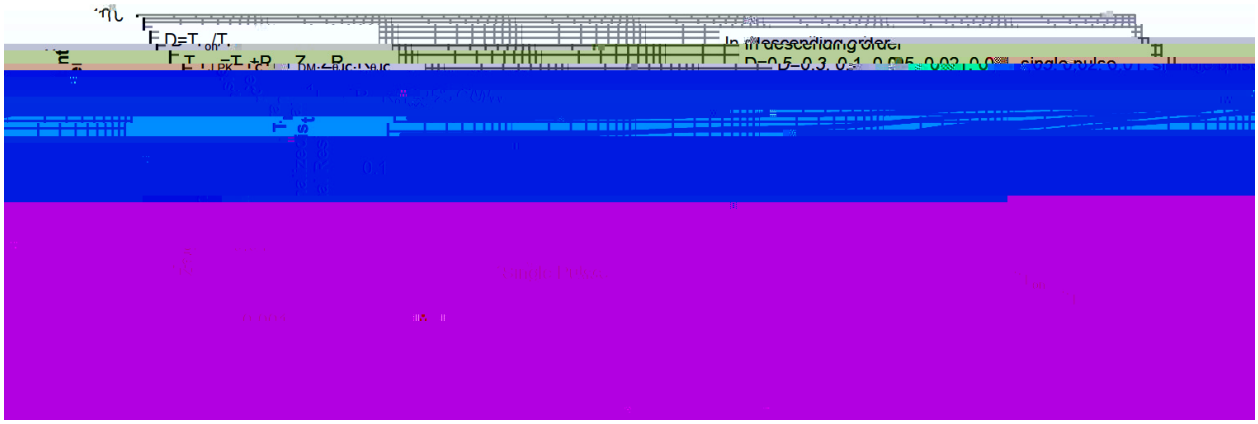
Figure 6: Body Diode Characteristics

Ô ? d • Ž ¢ / Electrical Characteristic Curve

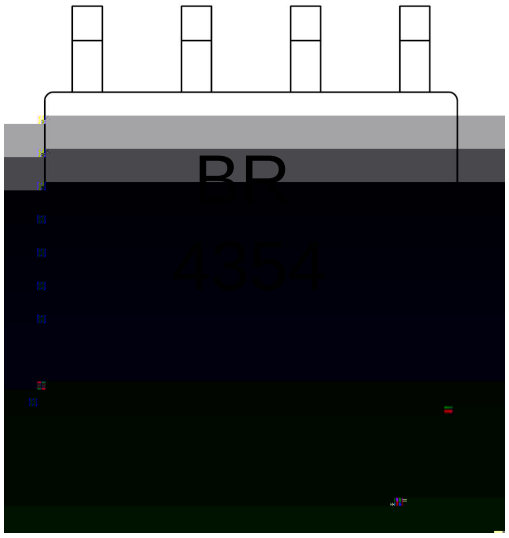








, M y ƒ / Marking Instructions



ª ¢ y

BR y ¸ [W A

y º Z W A

y ÿ D Z W A k š ÿ D Z J

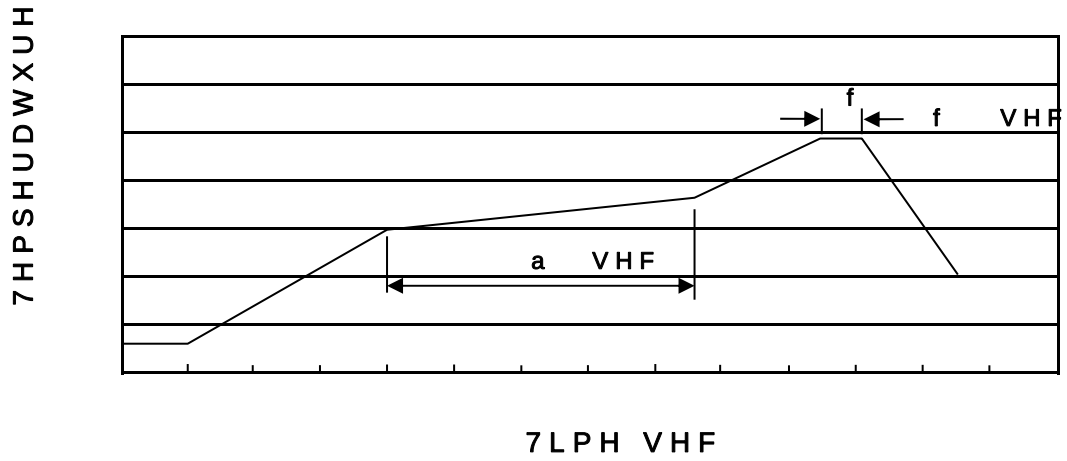
Note:

BR: Company Code.

4354 y Product Type.

****: Lot No. Code, code change with Lot No.

š WD t … • Ž ¢ (x /) / : K S V K X G Z [X K 6 X U L O R K L U X / 8 8 K L R U] 9 U R J K X O T M 6



7 L P H V H F

ª ¢ y

Note:

1o• Ä ½ “ † 150 ½180 - k ž • 60 ½90sec;

1.Preheating:150~180 - , Time:60~90sec.

2o• Q › “ † 245 r5 - k ž • 4 Ò 5 r0.5sec;

2.Peak Temp.:245 r5 - , Duration:5 r0.5sec.

3o•D N ò i Ò 0 , † 2 ½10 - /sec.

3. Cooling Speed: 2~10 - /sec.

ÂD /Cã p ¯ »] / Resistance to Soldering Heat Test Conditions

“ † y 260 r5 - ž • y 10 r1 sec. Temp.:260±5 Time:10±1 sec

G P á / Packaging SPEC.

2 & x / REEL

Package Type 7>û ˜ E	Units ;>û ¦H					Dimension ;>û p . (unit Æmm³)		
	Units/Reel / --	Reels/Inner Box -- /-	Units/Inner Box /-	Inner Boxes/Outer Box - /1ç	Units/Outer Box /1ç	Reel	Inner Box×	Outer Box1ç
SOP/ESOP-8	4,000	2	8,000	6	48,000	13 s ×12	360×360×50	380×335×366

„ Ð y ƒ / Notices